

SE85130GA

N-Channel Enhancement-Mode MOSFET

Revision: A

General Description

Advanced trench technology to provide excellent RDS(ON), low gate charge and low operation voltage. This device is suitable for using as a load switch or in PWM applications.

- Simple Drive Requirement
- Small Package Outline
- Surface Mount Device

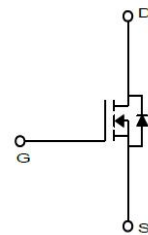
Features

For a single MOSFET

- $V_{DS} = 85V$
- $R_{DS(ON)} = 4.6m\Omega @ V_{GS}=10V$

Pin configurations

See Diagram below



Absolute Maximum Ratings

Parameter		Symbol	Rating	Units
Drain-Source Voltage		V_{DS}	85	V
Gate-Source Voltage		V_{GS}	± 20	V
Drain Current	Continuous	I_D	130	A
	Pulsed		320	
Single Pulse Avalanche Energy		E_{AS}	700	mJ
Total Power Dissipation	@TC=25°C	P_D	145	W
Operating Junction Temperature Range		T_J	-55 to 175	°C

SE85130GA

Electrical Characteristics (T _J =25°C unless otherwise noted)						
Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS (Note 2)						
B _V DSS	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0 V	85			V
I _{DSS}	Drain to Source Leakage Current	V _{DS} =85V, V _{GS} =0V			1	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =20V			100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D =250μA	2.5	3.3	4.5	V
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =55A	-	4.6	5.8	mΩ
g _{FS}	Forward Transconductance	V _{DS} =10V, I _D =55A	40			S
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =40V, f=1MHz		3870		pF
C _{oss}	Output Capacitance			500		pF
C _{rss}	Reverse Transfer Capacitance			43		pF
SWITCHING PARAMETERS						
Q _g	Total Gate Charge ²	V _{GS} =10V, V _{DS} =40V, I _D =55A		54		nC
Q _{gs}	Gate Source Charge			20		nC
Q _{gd}	Gate Drain Charge			9		nC
t _{d(on)}	Turn-On Delay Time	V _{GS} =10V, V _{DS} =40V, R _{GEN} =4.7Ω I _D =55A		18		ns
t _{d(off)}	Turn-Off Delay Time			28		ns
t _{d(r)}	Turn-On Rise Time			8		ns
t _{d(f)}	Turn-Off Fall Time			8		ns

Typical Characteristics

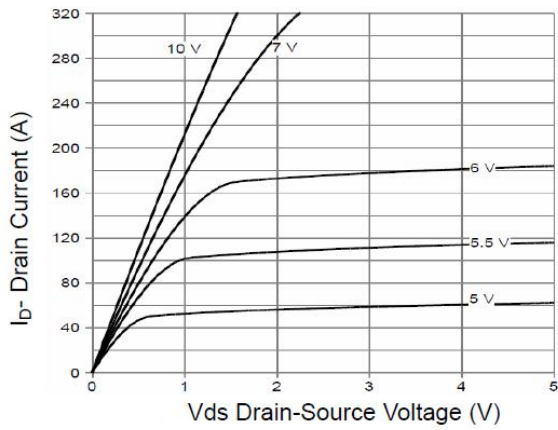


Figure 1 Output Characteristics

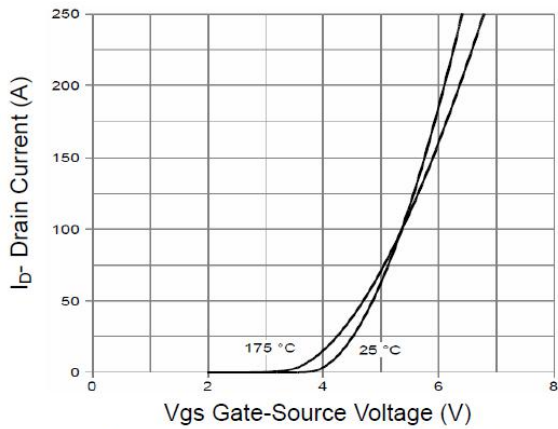


Figure 2 Transfer Characteristics

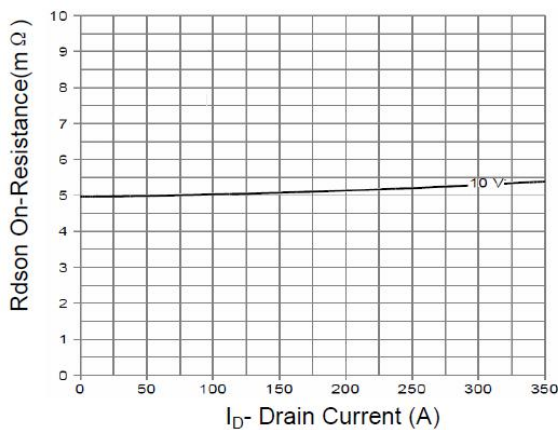


Figure 3 Rds(on)- Drain Current

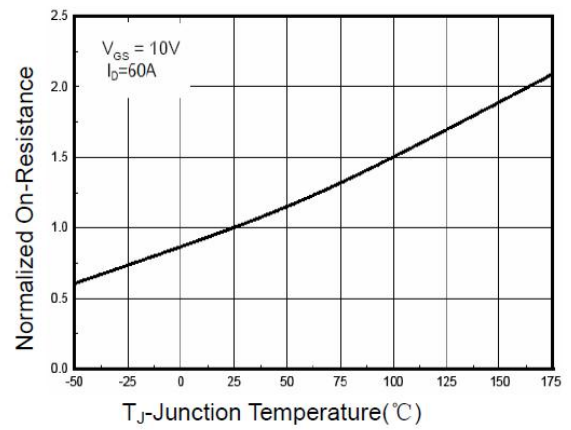


Figure 4 Rds(on)-Junction Temperature

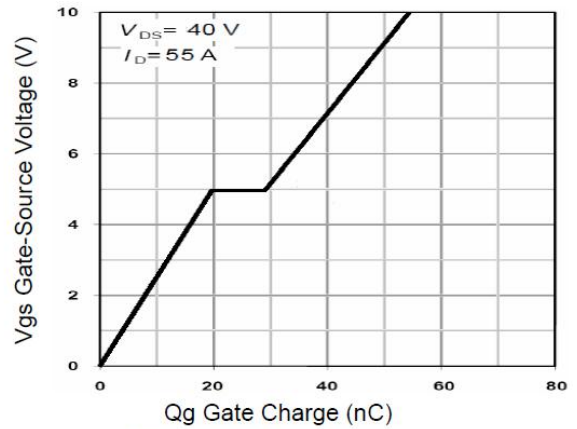


Figure 5 Gate Charge

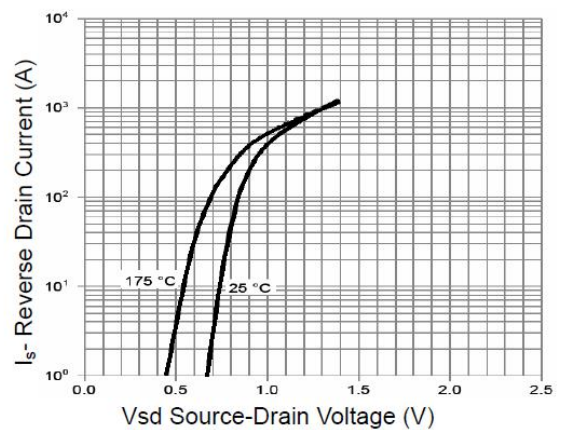


Figure 6 Source- Drain Diode Forward

Typical Characteristics

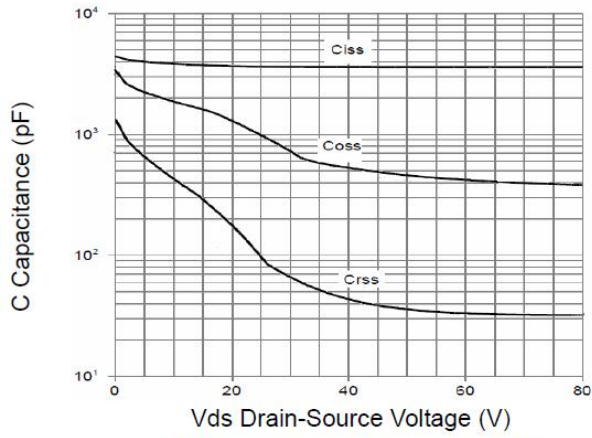


Figure 7 Capacitance vs Vds

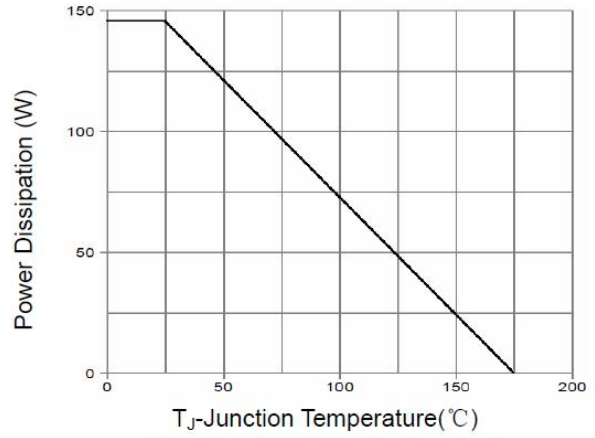


Figure 9 Power De-rating

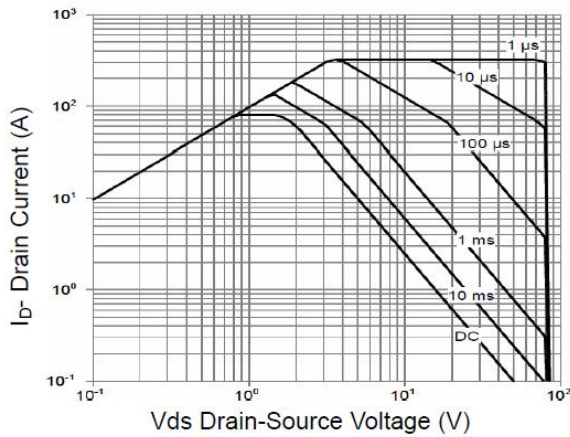


Figure 8 Safe Operation Area

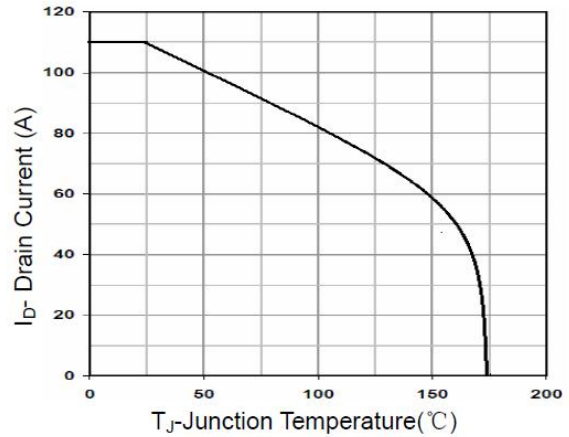


Figure 10 Current De-rating

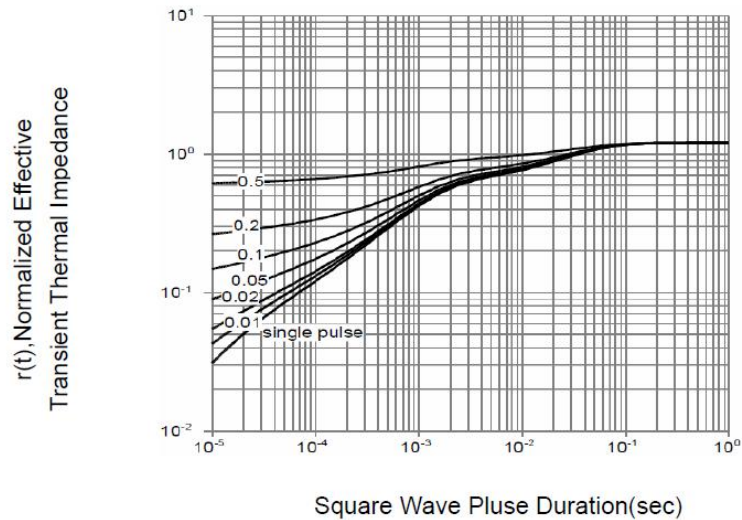
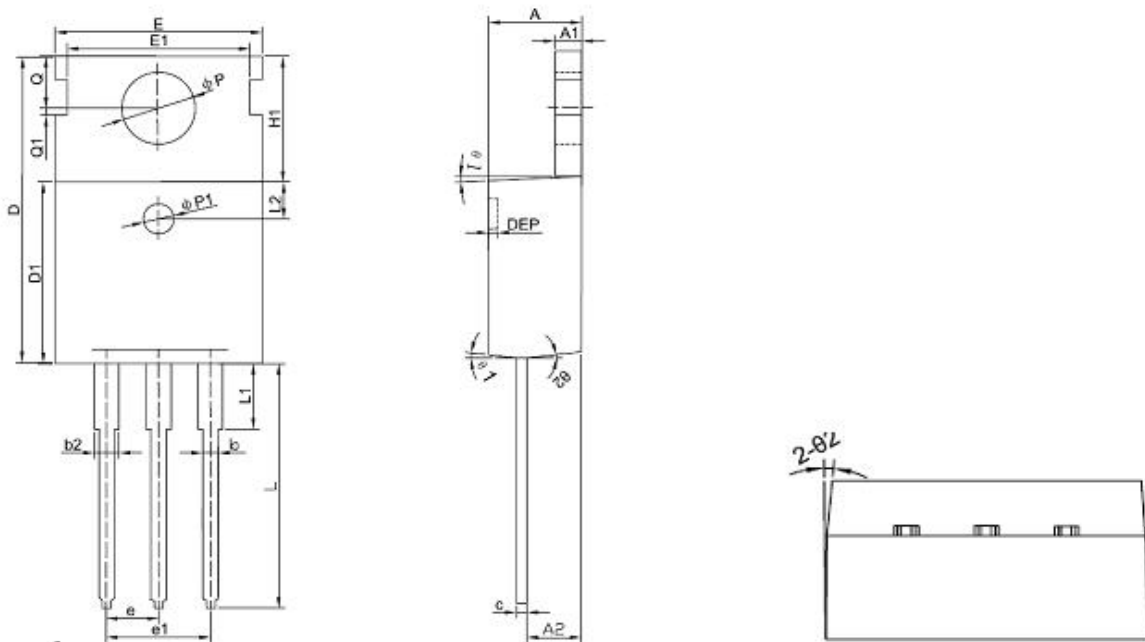


Figure 11 Normalized Maximum Transient Thermal Impedance

SE85130GA

Package Outline Dimension

TO-220



Symbol	Dimension In Millimeters			Dimension In Inches		
	Min	Nom	Max	Min	Nom	Max
A	4.400	4.550	4.700	0.173	0.179	0.185
A1	1.270	1.300	1.330	0.050	0.051	0.052
A2	2.590	2.690	2.790	0.102	0.106	0.110
b	0.770	-	0.900	0.030	-	0.035
b2	1.230	-	1.360	0.048	-	0.054
c	0.480	0.500	0.520	0.019	0.020	0.020
D	15.100	15.400	15.700	-	0.606	-
D1	9.000	9.100	9.200	0.354	0.358	0.362
DEP	0.050	0.285	0.520	0.002	0.011	0.020
E	10.060	10.160	10.260	0.396	0.400	0.404
E1	-	8.700	-	-	0.343	-
$\Phi P1$	1.400	1.500	1.600	0.055	0.059	0.063
e	2.54BSC			0.1BSC		
e1	5.08BSC			0.2BSC		
H1	6.100	6.300	6.500	0.240	0.248	0.256
L	12.750	12.960	13.170	0.502	0.510	0.519
L1	-	-	3.950	-	-	0.156
L2	1.85REF			0.073REF		
ΦP	3.570	3.600	3.630	0.141	0.142	0.143
Q	2.730	2.800	2.870	0.107	0.110	0.113
Q1	-	0.200	-	-	0.008	-
θ_1	5 ⁰	7 ⁰	9 ⁰	5 ⁰	7 ⁰	9 ⁰
θ_2	1 ⁰	3 ⁰	5 ⁰	1 ⁰	3 ⁰	5 ⁰

The SINO-IC logo is a registered trademark of ShangHai Sino-IC Microelectronics Co., Ltd.

© 2005 SINO-IC – Printed in China – All rights reserved.

SHANGHAI SINO-IC MICROELECTRONICS CO., LTD

Add: Building 3, Room 3401-03, No.200 Zhangheng Road, ZhangJiang Hi-Tech Park, Pudong,
Shanghai 201203, China

Phone: +86-21-33932402 33932403 33932405 33933508 33933608

Fax: +86-21-33932401

Email: webmaster@sino-ic.net

Website: <http://www.sino-ic.net>